

DESCRIPTION**TITLE OF THE INVENTION:**

BONDING WIRE FOR SEMICONDUCTOR DEVICES

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TECHNICAL FIELD

[0001] The present invention relates to a bonding wire for semiconductor devices. Furthermore, the present invention relates to a semiconductor device including the bonding wire.

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BACKGROUND ART

[0002] In semiconductor devices, electrodes formed on a semiconductor chip are connected with electrodes on a lead frame or a substrate using a bonding wire. A bonding process of a bonding wire is carried out by performing 1st bonding of a wire part onto an electrode on the semiconductor chip; forming a loop; and finally performing 2nd bonding of a wire part onto an external electrode such as the lead frame or the electrode on the substrate. In the 1st bonding, a tip end of wire is heated and molten by arc heat input to form a free air ball (FAB: Free Air Ball; hereinafter also simply referred to as "ball" or "FAB") through surface tension, and then this ball part is compression-bonded (hereinafter referred to as "ball-bonded") onto the electrode on the semiconductor chip. In the 2nd bonding, the wire part is compression-bonded (hereinafter referred to as "wedge-bonded") onto the external electrode by applying ultrasonic waves and load to the wire part without forming the ball.

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[0003] Gold (Au) has been the common material of the bonding wire, but has been being replaced with copper (Cu) mainly for LSI use (e.g., Patent Literatures 1 to 3).

Meanwhile, for on-vehicle device use on the background of recent proliferation of electric vehicles and hybrid vehicles, and further for power device (power semiconductor device) use in large power equipment such as air conditioners and photovoltaic power generation systems, there has been a growing demand for replacement with Cu that has high efficiency and reliability due to its high thermal conductivity and fusing current characteristic.

[0004] Cu has the drawback of being more susceptible to oxidation than Au. As a method of preventing the surface oxidation of the Cu bonding wire, there has been proposed a structure in which a surface of a Cu core material is coated with a metal such as Pd (Patent Literature 4). There has been also proposed a Pd-coated Cu bonding wire which has an improved bond reliability of the 1st bonding part by coating a surface of a Cu core material with Pd and adding Pd and Pt into the Cu core material (Patent Literature 5).

20 **RELATED ART REFERENCE**

Patent Literature

[0005] Patent Literature 1: JP-A-S61-48534
Patent Literature 2: JP-T-2018-503743
Patent Literature 3: WO 2017/221770
25 Patent Literature 4: JP-A-2005-167020
Patent Literature 5: WO 2017/013796

SUMMARY OF INVENTION

PROBLEM TO BE SOLVED BY THE INVENTION

30 [0006] The on-vehicle devices and the power devices tend to be exposed to higher temperature as compared with general electronic devices during operation, and the bonding wire used therefor is required to exhibit a

favorable bond reliability under a rigorous high-temperature environment.

[0007] The present inventors have conducted the evaluation based on characteristics required for the on-vehicle devices and the power devices and found that, in a conventional Cu bonding wire having a Pd-coating layer, the Pd-coating layer may sometimes be partially exfoliated during the bonding process of the wire, thereby causing exposure of the Cu core material, and as a result, a contact area between the Pd-coating part and the Cu-exposed part is exposed to an environment containing oxygen, water vapor, and sulfur compound-based outgas generated from a sealing resin under the high-temperature environment, resulting in local corrosion of Cu, that is, galvanic corrosion, which makes it difficult to sufficiently achieve the bond reliability of the 2nd bonding part. On the other hand, a bare Cu bonding wire without the Pd-coating layer provides a poor FAB shape and exhibits insufficient bondability of the 1st bonding part, although galvanic corrosion does not occur.

[0008] As described above, it is desired to develop a Cu-based bonding wire that achieves a favorable FAB shape and reduces a galvanic corrosion in a high-temperature environment to achieve a favorable bond reliability of the 2nd bonding part. In this regard, the characteristics required for the on-vehicle devices and the like are becoming more and more severe, and there is a demand for reliable operations at a higher temperature. In order to evaluate the bond reliability of the bonding wire in a high-temperature environment, a High Temperature Storage Life Test (HTSL) is often performed in which the wire is exposed to an environment with a temperature of 175°C by assuming a rigorous high-temperature environment. The

present inventors have performed HTSL with a temperature of 200°C by assuming a more rigorous high-temperature environment. As a result, it has been found that even the bonding wire that achieves a favorable bond reliability of the 2nd bonding part at a temperature of 175°C tends to lose the bond reliability of the 2nd bonding part at a temperature of 200°C. Furthermore, it has been confirmed that such a tendency becomes more significant as the wire diameter of the bonding wire becomes thicker. Regarding this, the fact that the deterioration of the bond reliability of the 2nd bonding part becomes significantly worse as the wire diameter becomes thicker cannot be explained on the basis of only a defective mode of a galvanic corrosion. Thus, the present inventors have also found that other defective modes are caused and become prominent in addition to the defective mode of the galvanic corrosion in a rigorous high-temperature environment with a temperature of 200°C or the like.

[0009] An object of the present invention is to provide a novel Cu bonding wire that achieves a favorable FAB shape and achieves a favorable bond reliability of the 2nd bonding part even in a rigorous high-temperature.

MEANS FOR SOLVING PROBLEM

[0010] As a result of earnest investigation as to the problem described above, the present inventors have found that the problem described above can be solved by the bonding wire having the configuration described below, and completed the present invention.

[0011] That is, the present invention includes the following content.

[1] A bonding wire for semiconductor devices, the bonding wire comprising:

a core material of Cu or Cu alloy; and

a coating layer having a total concentration of Pd and Ni of 90 atomic% or more formed on a surface of the core material, wherein

in a concentration profile in a depth direction of the wire obtained by performing measurement using Auger electron spectroscopy (AES) so that the number of measurement points in the depth direction is 50 or more for the coating layer,

a thickness of the coating layer is 10 nm or more and 130 nm or less,

an average value X is 0.2 or more and 35.0 or less

where X is defined as an average value of a ratio of a Pd concentration C_{Pd} (atomic%) to an Ni concentration C_{Ni} (atomic%), C_{Pd}/C_{Ni} , for all measurement points in the coating layer,

a total number of measurement points in the coating layer whose absolute deviation from the average value X is 0.3 X or less is 50% or more relative to a total number of measurement points in the coating layer, and

the bonding wire satisfies at least one of the following conditions (i) and (ii):

(i) a concentration of In relative to the entire wire is 1 ppm by mass or more and 100 ppm by mass or less; and

(ii) a concentration of Ag relative to the entire wire is 1 ppm by mass or more and 500 ppm by mass or less.

[2] The bonding wire according to [1], wherein the total number of measurement points in the coating layer whose absolute deviation from the average value X is 0.2 X or less is 50% or more relative to the total number of measurement points in the coating layer.

[3] The bonding wire according to [1] or [2], wherein when linearly approximating C_{Pd} or C_{Ni} by the method of least squares for all measurement points in the coating layer, a difference between a maximum value and a minimum value of the obtained approximate straight line in a depth range of the coating layer is 20 atomic% or less.

[4] The bonding wire according to any one of [1] to [3], wherein the concentration profile in the depth direction of the wire is obtained by performing the measurement using AES under the following <Condition> while digging down the wire from its surface in the depth direction by Ar sputtering:

<Condition> a center of width of a measuring surface is aligned with a center of width of the wire, the width of the measuring surface is 5% or more and 15% or less of a diameter of the wire, and a length of the measuring surface is five times the width of the measuring surface.

[5] The bonding wire according to any one of [1] to [4], wherein the bonding wire contains Au at a surface thereof.

[6] The bonding wire according to [5], wherein a concentration of Au at the surface of the wire is 10 atomic% or more and 90 atomic% or less.

[7] The bonding wire according to [6], wherein the concentration of Au at the surface of the wire is measured using AES under the following <Condition>:

<Condition> a center of width of a measuring surface is aligned with a center of width of the wire, the width of the measuring surface is 5% or more and 15% or less of a diameter of the wire, and a length of the measuring surface is five times the width of the measuring surface.

[8] The bonding wire according to any one of [1] to [7], wherein when forming a free air ball (FAB: Free Air Ball) by using the wire and then measuring crystal orientations

in a cross-section of the FAB perpendicular to a compression-bonding direction, a proportion of a crystal orientation $\langle 100 \rangle$ angled at 15° or less to the compression-bonding direction is 30% or more.

5 [9] The bonding wire according to [8], wherein the proportion of the crystal orientation $\langle 100 \rangle$ angled at 15° or less to the compression-bonding direction is 50% or more.

[10] The bonding wire according to any one of [1] to [9],
10 wherein

the bonding wire contains one or more elements selected from the group consisting of B, P and Mg (hereinafter referred to as a "first additive element"), and

15 a total concentration of the first additive element is 1 ppm by mass or more and 100 ppm by mass or less relative to the entire wire.

[11] The bonding wire according to any one of [1] to [10], wherein

20 the bonding wire contains one or more elements selected from the group consisting of Se, Te, As and Sb (hereinafter referred to as a "second additive element"), and

a total concentration of the second additive element
25 is 1 ppm by mass or more and 100 ppm by mass or less relative to the entire wire.

[12] The bonding wire according to any one of [1] to [11], wherein

the bonding wire contains one or more elements
30 selected from the group consisting of Ga and Ge (hereinafter referred to as a "third additive element"), and

a total concentration of the third additive element is 0.011% by mass or more and 1.5% by mass or less relative to the entire wire.

[13] A semiconductor device comprising the bonding wire
5 according to any one of [1] to [12].

EFFECT OF THE INVENTION

[0012] The present invention can provide the novel Cu bonding wire that achieves a favorable FAB shape and
10 achieves a favorable bond reliability of the 2nd bonding part even in a rigorous high-temperature.

BRIEF DESCRIPTION OF DRAWINGS

[0013] FIG. 1 is a schematic view illustrating a
15 position and dimensions of a measuring surface for performing a composition analysis using AES.

FIG. 2 is a schematic view illustrating a cross-section of FAB perpendicular to a compression-bonding direction.

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EMBODIMENT FOR CARRYING OUT THE INVENTION

[0014] Hereinafter, the present invention will be described in detail with reference to preferable embodiments thereof. Drawings may be referred to during
25 the explanation. However, note that each drawing schematically shows the shape, size and arrangement of constituent elements only to the extent that the invention can be understood. The present invention is not limited to the following embodiments and examples and may be modified
30 for implementation within the scope not departing from the scope of claims of the present invention and their equivalents.

[0015] [Bonding wire for semiconductor devices]

A bonding wire for semiconductor devices according to the present invention (hereinafter also simply referred to as "wire of the present invention" or "wire") is characterized in that the bonding wire includes:

5 a core material of Cu or Cu alloy; and

 a coating layer having a total concentration of Pd and Ni of 90 atomic% or more formed on a surface of the core material, wherein

 in a concentration profile in a depth direction of the wire obtained by performing measurement using Auger electron spectroscopy (AES) so that the number of measurement points in the depth direction is 50 or more for the coating layer,

 a thickness of the coating layer is 10 nm or more and 15 130 nm or less,

 an average value X is 0.2 or more and 35.0 or less where X is defined as an average value of a ratio of a Pd concentration C_{Pd} (atomic%) to an Ni concentration C_{Ni} (atomic%), C_{Pd}/C_{Ni} , for all measurement points in the coating layer,

 a total number of measurement points in the coating layer whose absolute deviation from the average value X is 0.3 X or less is 50% or more relative to a total number of measurement points in the coating layer, and

25 a concentration of at least one of In and Ag relative to the entire wire is 1 ppm by mass or more.

[0016] As described above, the bonding wires used for the on-vehicle devices and the power devices are required to exhibit a favorable bond reliability under a rigorous high-temperature environment. For example, the bonding wires used for the on-vehicle devices require the bond reliability in a high-temperature environment exceeding 30 150°C. The present inventors have conducted the evaluation

based on the characteristics required for the on-vehicle devices and the like and found that, in some cases, the conventional Cu bonding wires with the Pd-coating layers cause a galvanic corrosion in a high-temperature environment and fail to sufficiently achieve the bond reliability of the 2nd bonding parts. Furthermore, the bare Cu bonding wire without the Pd-coating layer does not cause a galvanic corrosion, but provides a poor FAB shape and consequently an inferior compression-bonding shape of the 1st bonding part and thus cannot be sufficiently applied for a narrow-pitch bonding required for high-density mounting.

[0017] The characteristics required for the on-vehicle devices and the like are becoming more and more severe, and there is a demand for reliable operations at a higher temperature. In order to evaluate the bond reliability of the bonding wire in a high-temperature environment, a High Temperature Storage Life Test (HTSL) is often performed in which the wire is exposed to an environment with a temperature of 175°C by assuming a rigorous high-temperature environment. The present inventors have performed HTSL with a temperature of 200°C by assuming a more rigorous high-temperature environment. As a result, it has been found that even the bonding wire that achieves a favorable bond reliability of the 2nd bonding part at a temperature of 175°C tends to lose the bond reliability of the 2nd bonding part at a temperature of 200°C.

Furthermore, it has been confirmed that such a tendency becomes more significant as the wire diameter of the bonding wire becomes thicker. Regarding this, the fact that the deterioration of the bond reliability of the 2nd bonding part becomes significantly worse as the wire

diameter becomes thicker cannot be explained on the basis of only a defective mode of a galvanic corrosion. Thus, it has also been found that other defective modes are caused and become prominent in addition to the defective mode of the galvanic corrosion in a rigorous high-temperature environment with a temperature of 200°C or the like.

[0018] In contrast, the present inventors have found that a favorable FAB shape can be achieved and a favorable bond reliability of the 2nd bonding part can be achieved even in a rigorous high-temperature environment, by using a bonding wire that includes:

a core material of Cu or Cu alloy; and

a coating layer having a total concentration of Pd and Ni of 90 atomic% or more formed on a surface of the core material, wherein

in a concentration profile in a depth direction of the wire obtained by performing measurement using AES so that the number of measurement points in the depth direction is 50 or more for the coating layer,

a thickness of the coating layer is 10 nm or more and 130 nm or less,

an average value X is 0.2 or more and 35.0 or less where X is defined as an average value of a ratio of a Pd concentration C_{Pd} (atomic%) to an Ni concentration C_{Ni} (atomic%), C_{Pd}/C_{Ni} , for all measurement points in the coating layer,

a total number of measurement points in the coating layer whose absolute deviation from the average value X is $0.3X$ or less is 50% or more relative to a total number of measurement points in the coating layer, and

a concentration of at least one of In and Ag relative to the entire wire is 1 ppm by mass or more. The present invention greatly contributes to putting a Cu bonding wire

into practical use in on-vehicle devices and power devices.

[0019] <Core material of Cu or Cu alloy>

The wire of the present invention includes a core material of Cu or Cu alloy (hereinafter, also simply referred to as "Cu core material").

[0020] The Cu core material is not particularly limited as long as it is made of Cu or Cu alloy, and there may be used a known Cu core material constituting a conventional Pd-coated Cu wire which has been known as a bonding wire for semiconductor devices.

[0021] In the present invention, the concentration of Cu in the Cu core material may be, for example, 97 atomic% or more, 97.5 atomic% or more, 98 atomic% or more, 98.5 atomic% or more, 99 atomic% or more, 99.5 atomic% or more, 99.8 atomic% or more, 99.9 atomic% or more, 99.98 atomic% or more, or 99.99 atomic% or more in the center (axial core part) of the Cu core material.

[0022] From the viewpoint of providing the bonding wire that achieves a favorable bond reliability of the 2nd bonding part in a rigorous high-temperature environment regardless of the wire diameter of the bonding wire, the Cu core material preferably includes In and Ag so that the concentration of at least one of In and Ag relative to the entire wire is 1 ppm by mass or more. A preferable range of the concentration of In and Ag relative to the entire wire is as described below.

[0023] The Cu core material may contain one or more dopants selected from the first additive element, the second additive element and the third additive element described later, for example. Preferable contents of these dopants are described later.

[0024] In an embodiment, the Cu core material consists of Cu and inevitable impurities. In another embodiment,

the Cu core material consists of Cu; at least one of In and Ag; and inevitable impurities. In yet another embodiment, the Cu core material consists of Cu; one or more elements selected from the first additive element, the second
5 additive element and the third additive element described later; and inevitable impurities. In yet another embodiment, the Cu core material consists of Cu; at least one of In and Ag; one or more elements selected from the first additive element, the second additive element and the
10 third additive element described later; and inevitable impurities. The term "inevitable impurities" used in relation to the Cu core material encompasses elements constituting the coating layer described later.

[0025] <Coating layer>

15 The wire of the present invention includes a coating layer having a total concentration of Pd and Ni of 90 atomic% or more (hereinafter, also simply referred to as a "coating layer") formed on a surface of the Cu core material.

20 [0026] In view of achieving a favorable FAB shape and achieves a favorable bond reliability of the 2nd bonding part in a high-temperature environment, it is important for the coating layer of the wire of the present invention to satisfy all of the following conditions (1) to (3) in a
25 concentration profile in the depth direction of the wire obtained by performing measurement using AES so that the number of measurement points in the depth direction is 50 or more for the coating layer (hereinafter also simply referred to as "concentration profile in the depth
30 direction of the wire").

(1) A thickness of the coating layer is 10 nm or more and 130 nm or less.

(2) An average value X is 0.2 or more and 35.0 or less

where X is defined as an average value of a ratio of a Pd concentration C_{Pd} (atomic%) to an Ni concentration C_{Ni} (atomic%), C_{Pd}/C_{Ni} , for all measurement points in the coating layer.

5 [0027] In the present invention, when obtaining the concentration profile in the depth direction of the wire by using AES, the measurement is performed so that the number of measurement points in the depth direction is 50 or more for the coating layer. In general, an analysis in the
10 depth direction using AES can be performed at measurement intervals of sub-nano order, thus it is relatively easy to set the number of the measurement points to 50 or more in relation to the thickness of the coating layer of the present invention. If the number of the measurement points
15 is less than 50 as a result of the measurement, the number of the measurement points is increased to 50 or more by lowering the sputtering rate, shortening the sputtering time, and the like, and then the measurement is performed again. This makes it possible to perform the measurement
20 using AES so that the number of measurement points in the depth direction is 50 or more for the coating layer and obtain the concentration profile in the depth direction of the wire. Although it depends on the thickness of the coating layer, it is more preferable to determine the AES
25 measurement point intervals such that the total number of measurement points in the coating layer becomes 70 or more (more preferably 100 or more). Accordingly, in a preferable embodiment, the coating layer of the wire of the present invention satisfies all of the above-mentioned
30 conditions (1) to (3) in the concentration profile in the depth direction of the wire obtained by performing the measurement using AES so that the number of measurement points in the depth direction is 50 or more for the coating

layer.

[0028] -Condition (1)-

 The condition (1) relates to the thickness of the coating layer. By including the coating layer that
5 satisfies the condition (1) in combination with the conditions (2) and (3), the wire of the present invention can achieve a favorable bond reliability of the 2nd bonding part in a high-temperature environment and can achieve a favorable FAB shape, and thus a favorable compression-
10 bonding shape of the 1st bonding part.

[0029] Regarding the condition (1), the thickness of the coating layer (the calculation method based on the concentration profile in the depth direction of the wire will be described below) is, from the viewpoint of
15 achieving a favorable FAB shape, 10 nm or more, preferably 12 nm or more, 14 nm or more, 15 nm or more, 16 nm or more, 18 nm or more, or 20 nm or more, more preferably 25 nm or more, 30 nm or more, 40 nm or more, or 50 nm or more, further preferably 60 nm or more, 70 nm or more, 80 nm or
20 more, or 90 nm or more. When the thickness of the coating layer is less than 10 nm, eccentricity tends to occur during the FAB formation, which deteriorates the FAB shape and the compression-bonding shape of the 1st bonding part. Furthermore, the upper limit of the thickness of the
25 coating layer is, from the viewpoint of achieving a favorable FAB shape, 130 nm or less, preferably 125 nm or less, 120 nm or less, 115 nm or less, or 110 nm or less. When the thickness of the coating layer is more than 130 nm, irregular shape and melting failure tend to occur
30 during the FAB formation, which deteriorates the FAB shape and also the compression-bonding shape of the 1st bonding part.

[0030] -Condition (2)-

The condition (2) relates to the average value X of the ratio of the Pd concentration C_{Pd} (atomic%) to the Ni concentration C_{Ni} (atomic%), C_{Pd}/C_{Ni} , for all measurement points in coating layer described above. By including the coating layer that satisfies the condition (2) in addition to the conditions (1) and (3), the wire of the present invention can achieve a favorable bond reliability of the 2nd bonding part in a high-temperature environment and can achieve a favorable FAB shape, and thus a favorable compression-bonding shape of the 1st bonding part.

[0031] Regarding the condition (2), the average value X is, from the viewpoint of achieving a favorable bond reliability of the 2nd bonding part, 35.0 or less, preferably 34.0 or less, more preferably 32.0 or less, 30.0 or less, 28.0 or less, 26.0 or less, 25.0 or less, 24.0 or less, 22.0 or less, or 20.0 or less. When the average value of the ratio C_{Pd}/C_{Ni} is more than 35.0, the galvanic corrosion cannot be reduced in a high-temperature environment, thereby often making it difficult to achieve sufficient high-temperature bond reliability of the 2nd bonding part. Furthermore, the lower limit of the average value X is, from the viewpoint of achieving a favorable bondability of the 2nd bonding part, 0.2 or more, preferably 0.4 or more, 0.5 or more, 0.6 or more, 0.8 or more, 1.0 or more, or more than 1.0, more preferably 1.5 or more, 2.0 or more, 2.5 or more, or 3.0 or more. When the average value X is less than 0.2, it is often difficult to achieve the sufficient bondability of the 2nd bonding part (initial bondability of the 2nd bonding part).

[0032] -Condition (3)-

The condition (3) relates to the total number of measurement points in the coating layer whose absolute deviation from the average value X described above is $0.3X$

or less being 50% or more relative to the total number of measurement points in the coating layer. By including the coating layer that satisfies the condition (3) in combination with the conditions (1) and (2), the wire of the present invention can achieve a favorable bond reliability of the 2nd bonding part in a high-temperature environment and can achieve a favorable FAB shape, and thus a favorable compression-bonding shape of the 1st bonding part.

[0033] The condition (3), together with the condition (2), indicates that the coating layer contains the Pd-Ni alloy, which contains Pd and Ni at a predetermined ratio, in a high concentration while reducing variations in a Pd/Ni ratio in the thickness direction of the coating layer. From the viewpoint of achieving a more favorable bond reliability of the 2nd bonding part in a high-temperature environment and achieving a more favorable FAB shape, it is more preferable that the total number of measurement points in the coating layer whose absolute deviation from the average value X is $0.2X$ or less (more preferably $0.18X$ or less, $0.16X$ or less, or $0.15X$ or less) is 50% or more relative to the total number of measurement points in the coating layer.

[0034] From the viewpoint of achieving a further favorable bond reliability of the 2nd bonding part in a high-temperature environment and achieving a further favorable FAB shape, the total number of measurement points in the coating layer whose absolute deviation from the average value X falls within a predetermined range (the preferred range is as described above) is preferably 55% or more or 60% or more, more preferably 65% or more, 70% or more, or 75% or more, further preferably 80% or more relative to the total number of measurement points in the

coating layer.

[0035] In the concentration profile in the depth direction of the wire, when linearly approximating the Pd concentration C_{Pd} (atomic%) or the Ni concentration C_{Ni} (atomic%) by the method of least squares for all measurement points in the coating layer, a difference between the maximum value and the minimum value of the obtained approximate straight line in the depth (thickness) range of the coating layer is preferably 20 atomic% or less, more preferably 15 atomic% or less, further preferably 10 atomic% or less, 8 atomic% or less, 6 atomic% or less, or 5 atomic% or less, from the viewpoint of further obtaining the effects of the present invention. Specifically, in a case where the average value X is less than 1, it is preferable that, when linearly approximating C_{Ni} (atomic%) by the method of least squares for all measurement points in the coating layer, the difference between the maximum value and the minimum value of the obtained approximate straight line in the depth range of the coating layer falls within the range described above. In a case where the average value X is 1 or more, it is preferable that, when linearly approximating C_{Pd} (atomic%) by the method of least squares for all measurement points in the coating layer, the difference between the maximum value and the minimum value of the obtained approximate straight line in the depth range of the coating layer falls within the range described above.

[0036] The thickness of the coating layer in the condition (1), the average value X and the absolute deviation from the average value X , the total number of the measurement points whose absolute deviation falls within the predetermined range, and the proportion of the total number of measurement points whose absolute deviation falls

within the predetermined range relative to the total number of measurement points in the coating layer in the conditions (2) and (3) can be confirmed and determined by performing a composition analysis using AES while digging
5 down the wire from its surface in the depth direction (direction to the center of the wire) by Ar sputtering. Specifically, a change in concentration of each element in the direction from the surface of the wire toward the depth (center) of the wire (so-called a concentration profile in
10 the depth direction) is obtained by performing 1) a composition analysis of the wire surface, and then repeating 2) a sputtering treatment with Ar and 3) a surface composition analysis after the sputtering treatment, and the above factors can be confirmed and
15 determined on the basis of the concentration profile. In the present invention, for obtaining the concentration profile in the depth direction, the unit of depth was in terms of SiO_2 .

[0037] When performing 1) the composition analysis of
20 the wire surface and 3) the surface composition analysis after the sputtering treatment, a position and dimensions of a measuring surface are determined as follows. In the following description, the width of the measuring surface indicates the dimension of the measuring surface in a
25 direction perpendicular to a wire axis (a thickness direction of the wire), and the length of the measuring surface indicates the dimension of the measuring surface in a direction along the wire axis (a length direction of the wire). A further description will be provided with
30 reference to FIG. 1. FIG. 1 is a schematic plan view illustrating a wire 1 in which the direction of the wire axis (the length direction of the wire) corresponds to the vertical direction (up-down direction) of FIG. 1 and the

direction perpendicular to the wire axis (the thickness direction of the wire) corresponds to the horizontal direction (left-right direction) of FIG. 1. FIG. 1 shows a measuring surface 2 in relation to the wire 1. The width of the measuring surface 2 is represented by a dimension w_a of the measuring surface in the direction perpendicular to the wire axis, and the length of measuring surface 2 is represented by a dimension l_a of the measuring surface in the direction of the wire axis.

[0038] The measuring surface is determined so that a center of width of the measuring surface is aligned with a center of width of the wire in the direction perpendicular to the wire axis, and the width of the measuring surface is 5% or more and 15% or less of a diameter of the wire. The length of the measuring surface is set to be five times the width of the measuring surface. In FIG. 1, the width of the wire is indicated by a symbol W , and the center of the width of the wire is indicated by a dashed line X . Thus, the measuring surface 2 is determined so that the center of width of the measuring surface 2 is aligned with the dashed line X indicating the center of width of the wire, and the width w_a of the measuring surface is 5% or more and 15% or less of the diameter of the wire (the same value as the width W of the wire), that is, $0.05W$ or more and $0.15W$ or less. Further, the length l_a of the measuring surface satisfies the relation of $l_a = 5w_a$. By determining the position and dimensions of the measuring surface as described above, it is possible to measure the success or failure of the conditions (1) to (3), which are required for achieving a favorable FAB shape as well as achieving a favorable bond reliability of the 2nd bonding part in a high-temperature environment, with high accuracy. Further, it is preferable to perform the measurement for measuring

surfaces at a plurality of points ($n \geq 3$) which are separated from each other by 1 mm or more in the direction of the wire axis, and employ an arithmetic average value thereof.

5 [0039] The thickness of the coating layer in the above-mentioned condition (1), the average value X and the absolute deviation from the average value X , the total number of measurement points whose absolute deviation falls within the predetermined range, and the proportion of the
10 total number of measurement points whose absolute deviation falls within the predetermined range relative to the total number of measurement points in the coating layer in the above-mentioned conditions (2) and (3) are based on results of measurement under the conditions described in [Thickness
15 analysis of coating layer using Auger electron spectroscopy (AES)] described later.

[0040] There will be described a tendency of the concentration profile in the depth direction obtained for the wire of the present invention according to an
20 embodiment. Up to a certain depth position from the surface of the wire, Pd and Ni tend to coexist at a certain ratio in a high concentration. That is, there is a region (coating layer) where the total concentration of Pd and Ni is 90 atomic% or more and, in such a region, there tends to
25 be a certain number of measurement points whose absolute deviation from the average value X is $0.3X$ or less where X is defined as an average value of the ratio of the Pd concentration C_{Pd} (atomic%) to the Ni concentration C_{Ni} (atomic%), C_{Pd}/C_{Ni} , for all measurement points in the
30 coating layer. Further proceeding in the depth direction, the concentration of Pd and Ni tends to be decreased and the concentration of Cu tends to be increased. By focusing on the Pd concentration C_{Pd} (atomic%) and the Ni

concentration C_{Ni} (atomic%) in such a concentration profile in the depth direction, it is possible to obtain the thickness and the total number of measurement points of the coating layer based on the thickness and the total number of measurement points of the region where the total concentration of Pd and Ni is 90 atomic% or more. Further, the average value X can be obtained by arithmetically averaging the ratio C_{Pd}/C_{Ni} for all measurement points in the coating layer, and the total number of measurement points whose absolute deviation from the average value X is 0.3 X or less can be obtained by confirming the absolute deviation of the ratio C_{Pd}/C_{Ni} from the average value X for all measurement points in the coating layer. In a case where the wire contains Au at a surface thereof as described below, the concentration of Au tends to be decreased and the concentration of Pd and Ni tends to be increased from the surface of the wire to a very shallow position in the concentration profile in the depth direction. In such a case as well, by focusing on the Pd concentration C_{Pd} (atomic%) and the Ni concentration C_{Ni} (atomic%), the thickness and the total number of measurement points of the coating layer can be obtained from the thickness and the total number of measurement points of the region where the total concentration of Pd and Ni is 90 atomic% or more. The average value X can be obtained by arithmetically averaging the ratio C_{Pd}/C_{Ni} for all measurement points in the coating layer, and the total number of measurement points whose absolute deviation from the average value X is 0.3 X or less can be obtained by confirming the absolute deviation of the ratio C_{Pd}/C_{Ni} from the average value X for all measurement points in the coating layer.

[0041] -Other preferable conditions for coating layer-

In the wire of the present invention, it is more preferable that the coating layer satisfies, in addition to all of the conditions (1) to (3) described above, one or both of the following conditions (4) and (5) based on the concentration profile in the depth direction of the wire.

(4) When defining the average value of the Pd concentration C_{Pd} (atomic%) for all measurement points in the coating layer as X_{Pd} , the total number of measurement points in the coating layer whose absolute deviation from the average value X_{Pd} is $0.1X_{Pd}$ or less is 50% or more relative to the total number of measurement points in the coating layer.

(5) When defining the average value of the Ni concentration C_{Ni} (atomic%) for all measurement points in the coating layer as X_{Ni} , the total number of measurement points in the coating layer whose absolute deviation from the average value X_{Ni} is $0.1X_{Ni}$ or less is 50% or more relative to the total number of measurement points in the coating layer.

Note that, in the conditions (4) and (5), the coating layer, the thickness thereof, and the total number of measurement points in the coating layer are as described above in relation to the conditions (1) to (3). The wire of the present invention including the coating layer that satisfies one or both of the conditions (4) and (5) in addition to the conditions (1) to (3) can achieve a particularly favorable bond reliability of the 2nd bonding part in a high-temperature environment and achieve a particularly favorable FAB shape.

[0042] The coating layer may contain one or more dopants selected from the first additive element, the second additive element and the third additive element described

later, for example. Preferable contents of these dopants are described later.

[0043] The wire of the present invention may further contain Au at a surface thereof. By further containing Au,
5 the bondability of the 2nd bonding part can be further improved.

[0044] From the viewpoint of further improving the bondability of the 2nd bonding part, the concentration of Au at the surface of the wire of the present invention is
10 preferably 10 atomic% or more, more preferably 15 atomic% or more, further preferably 20 atomic% or more, 22 atomic% or more, 24 atomic% or more, 25 atomic% or more, 26 atomic% or more, 28 atomic% or more, or 30 atomic% or more. From the viewpoint of achieving a favorable FAB shape and a
15 favorable compression-bonding shape of the 1st bonding part, the upper limit of the concentration of Au at the surface of the wire of the present invention is preferably 90 atomic% or less, more preferably 85 atomic% or less, further preferably 80 atomic% or less, 78 atomic% or less,
20 76 atomic% or less, 75 atomic% or less, 74 atomic% or less, 72 atomic% or less, or 70 atomic% or less. Accordingly, in a preferable embodiment, the concentration of Au at the surface of the wire of the present invention is 10 atomic% or more and 90 atomic% or less.

25 [0045] In the present invention, the concentration of Au at the surface can be determined by performing the composition analysis of the wire surface as a measuring surface using an Auger electron spectroscopy (AES) method. Herein, when determining the concentration of Au at the
30 surface, a gas component such as carbon (C), sulfur (S), oxygen (O) and nitrogen (N), a non-metal element, and the like are not considered.

[0046] The composition analysis of the wire surface can

be performed under the same conditions as in 1) the composition analysis of the wire surface described in relation to the method of obtaining the concentration profile in the depth direction. Specifically, when
5 performing the composition analysis of the wire surface using Auger electron spectroscopy (AES), the position and dimensions of the measuring surface are determined as follows.

10 The measuring surface is determined so that a center of width of the measuring surface is aligned with a center of width of the wire in the direction perpendicular to the wire axis, and the width of the measuring surface is 5% or more and 15% or less of a diameter of the wire. The length of the measuring surface is set to be five times the width
15 of the measuring surface. By determining the position and dimensions of the measuring surface as described above, it is possible to measure the concentration of Au at the surface, which is required for further improving the bondability of the 2nd bonding part, with high accuracy.

20 It is preferable to perform the measurement for measuring surfaces at a plurality of points ($n \geq 3$) which are separated from each other by 1 mm or more in the direction of the wire axis, and employ an arithmetic average value thereof.

25 [0047] The concentration of Au at the surface described above is based on a result of measurement under the conditions described in [Composition analysis of wire surface using Auger electron spectroscopy (AES)] described later.

30 [0048] In a case where the wire contains Au at the surface of the wire, a position indicating the maximum concentration of Au is closer to the surface of the wire than a position indicating the maximum concentration of Pd

in the concentration profile in the depth direction.

[0049] In the wire of the present invention, a boundary between the Cu core material and the coating layer is determined based on the total concentration of Pd and Ni in the concentration profile in the depth direction of the wire. The position at which the total concentration of Pd and Ni is 90 atomic% is determined as the boundary, and then a region where the total concentration of Pd and Ni is less than 90 atomic% is determined to be the Cu core material and a region where the total concentration of Pd and Ni is 90 atomic% or more is determined to be the coating layer. In the present invention, the boundary between the Cu core material and the coating layer is not necessarily a crystal grain boundary. The thickness of the coating layer can be determined, by confirming the concentration profile from the wire surface toward the center of the wire, as a distance from a depth position Z1 where the total concentration of Pd and Ni reaches 90 atomic% for the first time to a depth position Z2 where the total concentration of Pd and Ni decreases below 90 atomic% for the first time ($Z2 > Z1$).

[0050] The wire of the present invention is characterized by including the coating layer that satisfies the conditions (1) to (3) described above. The average value $\bar{X}$ and the absolute deviation from the average value $\bar{X}$, the total number of measurement points whose absolute deviation falls within the predetermined range, and the proportion of the total number of measurement points whose absolute deviation falls within the predetermined range relative to the total number of measurement points in the coating layer for the conditions (2) and (3) are determined by focusing on the Pd concentration C_{Pd} (atomic%) and the Ni concentration C_{Ni} (atomic%) in the coating layer

determined by the boundary determination method described above.

[0051] In an embodiment, the coating layer consists of Pd and Ni; and inevitable impurities. In another
5 embodiment, the coating layer consists of Pd and Ni; at least one of In and Ag; and inevitable impurities. In another embodiment, the coating layer consists of Pd and Ni; one or more elements selected from Au, the first additive element, the second additive element and the third
10 additive element described later; and inevitable impurities. In yet another embodiment, the coating layer consists of Pd and Ni; at least one of In and Ag; one or more elements selected from Au, the first additive element, the second additive element and the third additive element
15 described later; and inevitable impurities. The term "inevitable impurities" used in relation to the coating layer encompasses elements constituting the Cu core material.

[0052] The wire of the present invention is
20 characterized by including at least one of In and Ag. By including the coating layer that satisfies all of the conditions (1) to (3) described above and containing at least one of In and Ag in an amount of 1 ppm by mass or more relative to the entire wire, the wire of the present
25 invention can achieve a favorable FAB shape and achieves a favorable bond reliability of the 2nd bonding part in a high-temperature environment.

[0053] Thus, the wire of the present invention includes the coating layer that satisfies all of the conditions (1)
30 to (3) described above, and also satisfies at least one of the following conditions (i) and (ii).

(i) a concentration of In relative to the entire wire is 1 ppm by mass or more.

(ii) a concentration of Ag relative to the entire wire is 1 ppm by mass or more.

[0054] -Condition (i)-

The condition (i) relates to the concentration of In
5 relative to the entire wire. Regarding the condition (i),
from the viewpoint of providing the bonding wire that
achieves a favorable bond reliability of the 2nd bonding
part in a rigorous high-temperature environment regardless
of the wire diameter of the bonding wire, the concentration
10 of In relative to the entire wire is 1 ppm by mass or more,
preferably 2 ppm by mass or more, 3 ppm by mass or more, 4
ppm by mass or more, or 5 ppm by mass or more, more
preferably 6 ppm by mass or more, 8 ppm by mass or more, or
10 ppm by mass or more, further preferably 20 ppm by mass
15 or more, 30 ppm by mass or more, or 40 ppm by mass or more,
further, more preferably 50 ppm by mass or more. In
particular, it is preferable that the concentration of In
relative to the entire wire is 50 ppm by mass or more
because there can be readily provided the bonding wire that
20 achieves a favorable bond reliability of the 2nd bonding
part in a rigorous high-temperature environment regardless
of the wire diameter of the bonding wire. The upper limit
of the concentration of In relative to the entire wire can
be, for example, 100 ppm by mass or less, 95 ppm by mass or
25 less, 90 ppm by mass or less, or the like in consideration
of costs and the like because the effect of improving the
bond reliability of the 2nd bonding part in a high-
temperature environment is not further increased even when
the content exceeds this limit. Accordingly, in an
30 embodiment, when the wire of the present invention
satisfies the condition (i), the concentration of In
relative to the entire wire is 1 ppm by mass or more and
100 ppm by mass or less.

[0055] -Condition (ii)-

The condition (ii) relates to the concentration of Ag relative to the entire wire. Regarding the condition (ii), from the viewpoint of improving the bond reliability in a high-temperature environment, in particular, from the viewpoint of providing the bonding wire that achieves a favorable bond reliability of the 2nd bonding part in a rigorous high-temperature environment regardless of the wire diameter of the bonding wire, the concentration of Ag relative to the entire wire is 1 ppm by mass or more, preferably 2 ppm by mass or more, 3 ppm by mass or more, 4 ppm by mass or more, or 5 ppm by mass or more, more preferably 10 ppm by mass or more, 20 ppm by mass or more, 30 ppm by mass or more, 40 ppm by mass or more, or 50 ppm by mass or more, further preferably 60 ppm by mass or more or 80 ppm by mass or more, further more preferably 100 ppm by mass or more. In particular, it is preferable that the concentration of Ag relative to the entire wire is 100 ppm by mass or more because there can be readily provided the bonding wire that achieves a favorable bond reliability of the 2nd bonding part in a rigorous high-temperature environment regardless of the wire diameter. The upper limit of the concentration of Ag relative to the entire wire can be, for example, 500 ppm by mass or less, 480 ppm by mass or less, 460 ppm by mass or less, 450 ppm by mass or less, or the like in consideration of costs and the like because the effect of improving the bond reliability of the 2nd bonding part in a high-temperature environment is not further increased even when the content exceeds this limit. Accordingly, in an embodiment, when the wire of the present invention satisfies the condition (ii), the concentration of Ag relative to the entire wire is 1 ppm by mass or more and 500 ppm by mass or less.

[0056] When neither the condition (i) nor (ii) is satisfied, that is, when the concentration of both In and Ag relative to the entire wire is less than 1 ppm by mass, the bond reliability of the 2nd bonding part tends to
5 deteriorate in a rigorous high-temperature environments with a temperature of 200°C or the like. As mentioned above, this tendency becomes more significant as the wire diameter of the bonding wire becomes thicker.

[0057] Regarding the conditions (i) and (ii), the
10 preferable range of the concentration of In and Ag is as described above. In a more preferable embodiment, the wire of the present invention satisfies at least one of the following conditions (i) and (ii).

(i) The concentration of In relative to the entire
15 wire is 1 ppm by mass or more and 100 ppm by mass or more.

(ii) The concentration of Ag relative to the entire wire is 1 ppm by mass or more and 500 ppm by mass or more.

[0058] When at least one of the conditions (i) and (ii) is satisfied, from the viewpoint of more sufficiently
20 obtaining the effects of the present invention, the total concentration of In and Ag relative to the entire wire is 1 ppm by mass or more, preferably 2 ppm by mass or more, 3 ppm by mass or more, 4 ppm by mass or more, or 5 ppm by mass or more, more preferably 6 ppm by mass or more, 8 ppm
25 by mass or more, or 10 ppm by mass or more, further preferably 20 ppm by mass or more, 30 ppm by mass or more, or 40 ppm by mass or more, further more preferably 50 ppm by mass or more, 60 ppm by mass or more, or 70 ppm by mass or more. The upper limit is preferably 600 ppm by mass or
30 less, more preferably 550 ppm by mass or less, further preferably 500 ppm by mass or less.

[0059] In the wire of the present invention, In and Ag may be contained in either one of the Cu core material and

the coating layer or may be contained in both. From the viewpoint of providing the bonding wire that achieves a favorable bond reliability of the 2nd bonding part in a rigorous high-temperature environment regardless of the wire diameter of the bonding wire, In and Ag are preferably contained in the Cu core material.

[0060] The wire of the present invention may further contain one or more elements selected from the group consisting of B, P and Mg ("first additive element"). When the wire of the present invention contains the first additive element, the total concentration of the first additive element is preferably 1 ppm by mass or more relative to the entire wire. This makes it possible to provide a bonding wire that achieve a more favorable compression-bonding shape of the 1st bonding part. The total concentration of the first additive element relative to the entire wire is more preferably 2 ppm by mass or more, and further preferably 3 ppm by mass or more, 5 ppm by mass or more, 8 ppm by mass or more, 10 ppm by mass or more, 15 ppm by mass or more, or 20 ppm by mass or more. From the viewpoint of suppressing hardening of the wire and reducing chip damage at the time of 1st bonding, the total concentration of the first additive element is preferably 100 ppm by mass or less, and more preferably 90 ppm by mass or less, 80 ppm by mass or less, 70 ppm by mass or less, 60 ppm by mass or less or 50 ppm by mass or less.

Accordingly, in a preferable embodiment, the wire of the present invention contains the first additive element, and the total concentration of the first additive element is 1 ppm by mass or more and 100 ppm by mass or less relative to the entire wire.

[0061] When the wire of the present invention contains the first additive element, the first additive element may

be contained in either one of the Cu core material and the coating layer, or may be contained in both of them. When the wire of the present invention contains Au at a surface thereof, the first additive element may be contained

5 together with Au. The first additive element is preferably contained in the Cu core material from the viewpoint of providing a bonding wire that achieves a further favorable compression-bonding shape of the 1st bonding part.

[0062] The wire of the present invention may further
10 contain one or more elements selected from the group consisting of Se, Te, As and Sb ("second additive element"). When the wire of the present invention contains the second additive element, the total concentration of the second additive element is preferably 1 ppm by mass or more
15 relative to the entire wire. This makes it possible to improve the bond reliability of the 1st bonding part in a high-temperature and high-humidity environment. The total concentration of the second additive element relative to the entire wire is more preferably 2 ppm by mass or more,
20 and further preferably 3 ppm by mass or more, 5 ppm by mass or more, 8 ppm by mass or more, 10 ppm by mass or more, 15 ppm by mass or more, or 20 ppm by mass or more. From the viewpoint of achieving a favorable FAB shape and a favorable compression-bonding shape of the 1st bonding
25 part, the total concentration of the second additive element is preferably 100 ppm by mass or less, and further preferably 90 ppm by mass or less, 80 ppm by mass or less, 70 ppm by mass or less, 60 ppm by mass or less, or 50 ppm by mass or less. Accordingly, in a preferable embodiment,
30 the wire of the present invention contains the second additive element, and the total concentration of the second additive element is 1 ppm by mass or more and 100 ppm by mass or less relative to the entire wire.

[0063] When the wire of the present invention contains the second additive element, the second additive element may be contained in either one of the Cu core material and the coating layer, or may be contained in both of them.

5 From the viewpoint of providing a bonding wire that achieves a further favorable bond reliability of the 1st bonding part in a high-temperature and high-humidity environment, the second additive element is preferably contained in the coating layer. When the wire of the
10 present invention contains Au at a surface thereof, the second additive element may be contained together with Au

[0064] The wire of the present invention may further contain one or more elements selected from the group consisting of Ga and Ge ("third additive element"). When
15 the wire of the present invention contains the third additive element, the total concentration of the third additive element is preferably 0.011% by mass or more relative to the entire wire. This makes it possible to improve the bond reliability of the 1st bonding part in a
20 high-temperature environment. The total concentration of the third additive element relative to the entire wire is more preferably 0.015% by mass or more, and more preferably 0.02% by mass or more, 0.025% by mass or more, 0.03% by mass or more, 0.031% by mass or more, 0.035% by mass or
25 more, 0.04% by mass or more, 0.05% by mass or more, 0.07% by mass or more, 0.09% by mass or more, 0.1% by mass or more, 0.12% by mass or more, 0.14% by mass or more, 0.15% by mass or more, or 0.2% by mass or more. From the viewpoint of achieving a favorable FAB shape, a favorable
30 compression-bonding shape of the 1st bonding part, and a favorable bondability of the 2nd bonding part, the total concentration of the third additive element is preferably 1.5% by mass or less, and more preferably 1.4% by mass or

less, 1.3% by mass or less or 1.2% by mass or less.

Accordingly, in a preferable embodiment, the wire of the present invention contains the third additive element, and the total concentration of the third additive element is
5 0.011% by mass or more and 1.5% by mass or less relative to the entire wire.

[0065] When the wire of the present invention contains the third additive element, the third additive element may be contained in either one of the Cu core material and the
10 coating layer, or may be contained in both of them. When the wire of the present invention contains Au at a surface thereof, the third additive element may be contained together with Au.

[0066] The contents of In, Ag, the first additive
15 element, the second additive element and the third additive element in the wire can be measured by the method described in [Measurement of element content] described later.

[0067] In the wire of the present invention, the total concentration of Cu, Ni, Au and Pd is, for example, 98.4%
20 by mass or more, 98.5% by mass or more, 98.6% by mass or more, or 98.7% by mass or more and the like.

[0068] -Other preferable conditions-

There will be described preferable conditions that the wire of the present invention further satisfies. [0069]

25 When forming the FAB by using the wire of the present invention and then measuring crystal orientations in a cross-section of the FAB perpendicular to a compression-bonding direction, it is preferable that a proportion of a crystal orientation <100> angled at 15° or less to the
30 compression-bonding direction is 30% or more. This can achieve a particularly favorable compression-bonding shape of the 1st bonding part.

[0070] As described above, the bonding process with a

bonding wire is carried out by performing 1st bonding of a wire part onto an electrode on the semiconductor chip; forming a loop; and finally performing 2nd bonding of a wire part onto an external electrode such as the lead frame or the electrode on the substrate. In the 1st bonding, a tip end of wire is heated and molten by arc heat input to form an FAB through surface tension, and then this FAB is compression-bonded (ball-bonded) onto the electrode on the semiconductor chip. The present inventors have found that a particularly favorable compression-bonding shape of the 1st bonding part can be achieved by a wire ensuring that, when forming an FAB by using the wire and then measuring crystal orientations in a cross-section of the FAB perpendicular to a compression-bonding direction, a proportion of a crystal orientation $\langle 100 \rangle$ angled at 15° or less to the compression-bonding direction (hereinafter also simply referred to as a "proportion of the crystal orientation $\langle 100 \rangle$ in the cross-section of the FAB") is 30% or more.

[0071] From the viewpoint of achieving a further favorable compression-bonding shape of the 1st bonding part, the proportion of the crystal orientation $\langle 100 \rangle$ in the cross-section of the FAB is more preferably 35% or more, further preferably 40% or more, further more preferably 45% or more, particularly preferably 50% or more, 55% or more, or 60% or more. In particular, the wire ensuring the proportion of the crystal orientation $\langle 100 \rangle$ in the cross-section of the FAB of 50% or more can achieve a particularly favorable compression-bonding shape of the 1st bonding part. Accordingly, in a preferable embodiment, the proportion of the crystal orientation $\langle 100 \rangle$ in the cross-section of the FAB is 30% or more, more preferably 50% or more. The upper limit of the proportion of the crystal

orientation $\langle 100 \rangle$ in the cross-section of the FAB is not particularly limited and may be, for example, 100%, 99.5% or less, 99% or less, 98% or less, or the like.

[0072] There will be described the cross-section of the
5 FAB perpendicular to the compression-bonding direction with reference to FIG. 2. FIG. 2 shows a schematic view where a tip end of the wire 1 is heated and molten by arc heat input to form an FAB 10 through surface tension. The FAB 10 thus formed is compression-bonded to an electrode (not
10 shown) on a semiconductor chip. In FIG. 2, the compression-bonding direction of the FAB 10 is a direction indicated by an arrow Z (vertical direction (up-down direction) in FIG. 2). The cross-section perpendicular to the compression-bonding direction Z is a cross-section to
15 be exposed by cutting the FAB along a dashed line A-A perpendicular to the direction Z. Herein, the dashed line A-A serving as a reference for the process of exposing a cross-section is set at a position where the diameter of the exposed cross-section becomes maximum, that is, a
20 position where the diameter of the exposed cross-section becomes D when defining the diameter of the FAB as D. The straight line A-A may be deviated from the intended position in the process of exposing the cross-section, and the diameter of the exposed cross-section may be smaller
25 than D. However, as long as the diameter of the exposed cross-section is 0.9D or more, such a deviation is acceptable because the effect of the deviation on the proportion of the crystal orientation is negligibly small.

[0073] The crystal orientation in the cross-section of
30 the FAB perpendicular to the compression-bonding direction can be measured using an Electron Backscattered Diffraction (EBSD) method. The measuring device used for the EBSD method includes a scanning electron microscope and a

detector attached thereto. In the EBSD method, a diffraction pattern of reflected electrons generated by irradiating a sample with an electron beam is projected onto the detector, and the diffraction pattern is analyzed to determine the crystal orientation at each measurement point. For analyzing data obtained by the EBSD method, a dedicated software (OIM analysis manufactured by TSL Solutions, for example) can be used. The proportion of a specific crystal orientation can be calculated by inspecting the cross-section of the FAB perpendicular to the compression-bonding direction as an inspection surface, and using an analysis software dedicated to the measuring device.

[0074] In the present invention, the proportion of the crystal orientation $\langle 100 \rangle$ in the cross-section of the FAB is defined as a percentage of the area of the crystal orientation $\langle 100 \rangle$ relative to the measurement area. For calculating the proportion, only the crystal orientations that can be identified on the basis of a certain degree of reliability in the measuring surface are used. A portion where crystal orientation cannot be measured or a portion where the reliability of orientation analysis is low even when crystal orientation can be measured, and the like are excluded from the calculation of the measurement area and the area of the crystal orientation $\langle 100 \rangle$. If the excluded data exceed, for example, 20% relative to the entire data, it is highly possible that there has been some kind of contamination in the measurement object. Thus, the measurement needs to be performed again from the process of exposing the cross-section. Further, in the present invention, the proportion of the crystal orientation $\langle 100 \rangle$ in the cross-section of the FAB is obtained as the arithmetic average value of the proportion values obtained

by measuring three or more FABs.

[0075] The present inventors infer as follows about the reason why the wire having the proportion of the crystal orientation $\langle 100 \rangle$ in the cross-section of the FAB of 30% or more can achieve a particularly favorable compression-bonding shape of the 1st bonding part.

[0076] It is known that metal is deformed by slipping on a specific crystal plane or in a specific crystal direction (the plane and the direction are also called "slip plane" and "slip direction", respectively). The FAB formed using the wire of the present invention is mainly composed of Cu or Cu alloy serving as a core material, and its crystal structure is a face-centered cubic structure. In a case of having such a crystal structure, if the crystal orientation in the cross-section perpendicular to the compression-bonding direction is $\langle 100 \rangle$, the metal slips in the direction of 45 degrees relative to the compression-bonding surface and deforms. As a result, the FAB deforms in the direction of 45 degrees relative to the compression-bonding surface and deforms while radially spreading relative to the plane parallel to the compression-bonding surface. As a result, it is inferred that the compression-bonding shape becomes closer to a true circle.

[0077] In the present invention, the proportion of the crystal orientation $\langle 100 \rangle$ in the cross-section of the FAB tends to fall within a desired range by adjusting the thickness of the coating layer, the concentration ratio of Pd and Ni in the coating layer, and the Cu purity of the core material. For example, the present inventors infer as follows about the reason why the thickness of the coating layer has the effect on the proportion of the crystal orientation $\langle 100 \rangle$ in the cross-section of the FAB.

Specifically, it is considered that, during the melting stage, Pd and Ni in the coating layer are moderately diffusion-mixed toward the center of the FAB, and Cu or Cu alloy that contains the moderately diffusion-mixed Pd and Ni in a solid solution form is oriented in the crystal orientation <100> relative to the compression-bonding direction. Further, it is inferred that, when the thickness of the coating layer falls within the predetermined range, the diffusion-mixing of Pd and Ni during melting becomes moderate, thereby facilitating the alignment of the crystal orientation <100> relative to the compression-bonding direction. On the other hand, if the thickness of the coating layer is too thin, the crystal orientation tends to be random without orientation and if the thickness of the coating layer is too thick, other crystal orientations tend to be predominant.

[0078] The diameter of the wire of the present invention is not particularly limited and may be appropriately determined according to a specific purpose. Preferably, the diameter of the wire may be 30 μm or more, 35 μm or more, or 40 μm or more, for example. The upper limit of the diameter is not particularly limited and may be 80 μm or less, 70 μm or less, or 50 μm or less, for example.

[0079] <Manufacturing method of wire>
There will be described an example of a method for manufacturing the bonding wire for semiconductor devices according to the present invention.

[0080] First, raw material copper of high purity (4N to 6N; 99.99 to 99.9999% by mass or more) is processed into a large diameter (diameter of about 3 to 6 mm) by continuous casting to obtain an ingot.

[0081] In a case of adding a dopant such as In and Ag

and if added, the first additive element, the second additive element and the third additive element described above, examples of an addition method therefor may include a method of causing the dopant to be contained in the Cu core material, a method of causing the dopant to be contained in the coating layer, a method of depositing the dopant on the surface of the Cu core material, and a method of depositing the dopant on the surface of the coating layer. These methods may be combined with each other. The effect of the present invention can be achieved by employing any addition method. In the method of causing the dopant to be contained in the Cu core material, a copper alloy containing a required concentration of dopant may be used as a raw material to manufacture the Cu core material. In a case of obtaining such a copper alloy by adding the dopant to Cu as the raw material, a dopant component having high purity may be directly added to Cu, or alternatively, a mother alloy containing a dopant component at a concentration of about 1% may be used. In the method of causing the dopant to be contained in the coating layer, the dopant may be contained in Pd, Ni plating bath at the time of forming the coating layer (in a case of wet plating), or in a target material (in a case of dry plating). In the method of depositing the dopant on the surface of the Cu core material and the method of depositing the dopant on the surface of the coating layer, at least one type of deposition treatment selected from (1) application of aqueous solution ⇒ drying ⇒ heat treatment, (2) a plating method (wet), and (3) a vapor deposition method (dry) may be performed while the surface of the Cu core material or the surface of the coating layer being as a deposition surface.

[0082] The ingot having a large diameter is subjected to

forging, rolling, and wire-drawing to manufacture a wire with a diameter of about 0.7 to 2.0 mm (hereinafter also referred to as an "intermediate wire").

[0083] As a method for forming the coating layer on the surface of the Cu core material, an electroplating, an electroless plating, a vapor deposition, and the like can be used. Among them, the electroplating is preferable industrially because it can stably control film thickness. For example, the coating layer may be formed on the surface of the intermediate wire. The coating layer may be deposited at a stage of the ingot having large diameter, or the coating layer may be formed on the surface of the Cu core material after further thinning the intermediate wire by performing the wire-drawing (for example, after carrying out the wire-drawing to a final diameter of the Cu core material). The coating layer may be formed by, for example, providing a Pd-Ni alloy layer containing Pd and Ni at a predetermined ratio on the surface of the Cu core material. Alternatively, from the viewpoint of forming the coating layer with an excellent adhesiveness to the Cu core material, the coating layer may be formed by performing a strike plating with conductive metal on the surface of the Cu core material and then providing the Pd-Ni alloy layer containing Pd and Ni at the predetermined ratio thereon. Further, after forming the Pd-Ni alloy layer containing Pd and Ni at the predetermined ratio, a layer containing at least one of Pd and Ni (e.g., a Pd layer, an Ni layer, or a Pd-Ni alloy layer) may be further provided.

[0084] In a case of forming the wire containing Au at the surface thereof, the wire can be formed by providing an Au layer on the surface of the coating layer by the same method as described above.

[0085] The wire-drawing process can be performed by

using a continuous wire-drawing machine in which a plurality of diamond-coated dies can be set. If necessary, heat treatment may be performed during the wire-drawing process. In the case of forming the wire containing Au at the surface thereof, the constituent elements are diffused to each other between the Au layer at the surface of the wire and the lower Pd-Ni alloy layer (the Pd layer, the Ni layer, or the Pd-Ni alloy layer, if provided) by the heat treatment, which makes it possible to form a region containing Au (e.g., an alloy region containing Au, Pd and Ni) at the surface of the wire so that the concentration of Au at the surface of the wire falls within the preferable range described above. As a method therefor, a method that promotes alloying by continuously sweeping the wire at a constant speed in an electric furnace at a constant furnace temperature is preferable in that the composition and thickness of the alloy can surely be controlled. In substitution for the method of forming the region containing Au by providing the Au layer on the surface of the coating layer and then performing the heat treatment, a method of depositing an alloy region originally containing Au and at least one of Pd and Ni may be employed.

[0086] The wire of the present invention can achieve a favorable FAB shape and achieves a favorable bond reliability of the 2nd bonding part in a high-temperature environment. Thus, the bonding wire of the present invention can be suitably used as bonding wires particularly for on-vehicle devices and power devices.

[0087] [Method for manufacturing semiconductor device]
The semiconductor device can be manufactured by connecting the electrode on the semiconductor chip to the lead frame or the electrode on the circuit board by using the bonding wire for semiconductor devices of the present

invention.

[0088] In an embodiment, the semiconductor device according to the present invention includes a circuit board, a semiconductor chip, and a bonding wire for electrically connecting the circuit board and the semiconductor chip with each other, and is characterized in that the bonding wire is the wire of the present invention.

[0089] In the semiconductor device according to the present invention, the circuit board and the semiconductor chip are not particularly limited, and a known circuit board and semiconductor chip that may be used for constituting the semiconductor device may be used.

Alternatively, a lead frame may be used in place of the circuit board. For example, like the semiconductor device disclosed in JP 2020-150116 A, the semiconductor device may include a lead frame and a semiconductor chip mounted on the lead frame.

[0090] Examples of the semiconductor device may include various semiconductor devices used for electric products (for example, a computer, a cellular telephone, a digital camera, a television, an air conditioner, a solar power generation system), vehicles (for example, a motorcycle, an automobile, an electric train, a ship, and an aircraft), and the like.

Examples

[0091] There will be specifically described the present invention with Examples. However, the present invention is not limited to the Examples described below.

[0092] (Sample)

First, the method of preparing a sample will be described. For Cu as a raw material of the Cu core material, Cu having a purity of 99.99% by mass or more (4N)

with the balance composed of inevitable impurities was used. For In and Ag, and if added, the first additive element, the second additive element or the third additive element, these additive element having a purity of 99% by mass or more with the balance composed of inevitable impurities were used, or alternatively a mother alloy of Cu with a high concentration of these additive elements was used.

[0093] For the Cu alloy as the core material, the raw material was first charged into a graphite crucible and melted by heating to 1090 to 1500°C in an inert atmosphere such as an N₂ gas or Ar gas using a high-frequency furnace. Then, an ingot with a diameter of 3 to 6 mm was obtained by continuous casting. Next, the ingot thus obtained was drawn to manufacture an intermediate wire with a diameter of 0.7 to 2.0 mm, and then, wire-drawing processing and the like were continuously performed thereon using dies to further reduce the diameter of the wire to be coated. In the wire drawing process, a commercially available lubricant was used, and the wire-drawing speed was set to 20 to 150 m/min. For forming the coating layer, an acid washing with hydrochloric acid or sulfuric acid was performed to remove an oxide film on the wire surface, and then a Pd-Ni alloy layer containing Pd and Ni at a predetermined ratio was formed so as to cover the entire surface of the Cu alloy as the core material. Furthermore, in some wires (Example Nos. 16 to 19, 33 to 36, 43 to 46, 50, 54, and 55), an Au layer was provided on the Pd-Ni alloy layer. An electroplating method was used for forming the Pd-Ni alloy layer and the Au layer. As a Pd-Ni plating liquid and an Au plating liquid, commercially available plating liquids were prepared and used after appropriately adjusted.

[0094] Thereafter, the wire was further subjected to wire-drawing processing and the like to be processed to have a final wire diameter of $\phi 20 \mu\text{m}$. During the wire-drawing processing, intermediate heat treatment was
5 performed 1 to 2 times at 300 to 700°C for 2 to 15 seconds as needed. The intermediate heat treatment was performed while continuously sweeping the wire under flowing of an N₂ gas or Ar gas. After the wire was processed to have the final wire diameter, a refining heat treatment was
10 performed while continuously sweeping the wire under flowing of an N₂ gas or Ar gas. The heat treatment temperature for the refining heat treatment was 200 to 600°C, the wire feeding speed was 20 to 200 m/min, and the heat treatment time was 0.2 to 1.0 seconds. If the coating
15 layer was thin, the heat treatment temperature was set to be lower and the wire feeding speed was set to be higher. If the coating layer was thick, the heat treatment temperature was set to be higher and the wire feeding speed was set to be lower.

20 [0095] (Test and evaluation methods)

 There will be described test and evaluation methods.

[0096] [Composition analysis of wire surface using Auger electron spectroscopy (AES)]

 Regarding the wire containing Au at the surface of the
25 wire, the concentration of Au at the surface of the wire was determined by performing a measurement using the Auger electron spectroscopy (AES) where the measuring surface was a surface of the wire as follows.

 First, the bonding wire to be measured was fixed to
30 the sample holder in a linear arrangement. Next, the measuring surface was determined so that the center of width of the measuring surface was aligned with the center of width of the wire in the direction perpendicular to the

wire axis, and the width of the measuring surface was 5% or more and 15% or less of the diameter of the wire. The length of the measuring surface was set to be five times the width of the measuring surface. With using an AES
5 device (PHI-700 manufactured by ULVAC-PHI, INC.), the composition analysis was performed on the surface of the wire under a condition of acceleration voltage of 10 kV to obtain a surface Au concentration (atomic%).

The composition analysis using the AES was performed
10 on the measuring surfaces at three points which were separated from each other by 1 mm or more in the direction of the wire axis, and an arithmetic average value thereof was employed. When determining the concentration of Au at the surface, a gas component such as carbon (C), sulfur
15 (S), oxygen (O), or nitrogen (N), a nonmetallic element, and the like were not considered.

[0097] [Thickness analysis of coating layer using Auger electron spectroscopy (AES)]

A depth analysis using AES was used for the thickness
20 analysis of the coating layer. The depth analysis using AES analyzes a change in a composition in the depth direction by alternately performing a composition analysis and sputtering, so that a change in concentration of each element in the direction from the surface of the wire
25 toward the depth (center) of the wire (so-called a concentration profile in the depth direction) can be obtained.

Specifically, the concentration profile in the depth direction was obtained with AES by performing 1) a
30 composition analysis of the wire surface, and then repeating 2) a sputtering treatment with Ar and 3) a surface composition analysis after the sputtering treatment. The sputtering treatment in 2) was performed at

an acceleration voltage of 2 kV with Ar⁺ ion. In the surface composition analysis in 1) and 3), the dimensions of the measuring surface and the conditions for the composition analysis by the AES were the same as those described in [Composition analysis of wire surface using Auger electron spectroscopy (AES)] described above. For obtaining the concentration profile in the depth direction using AES, the measurement was performed so that the number of measurement points in the depth direction is 50 or more for the coating layer.

The concentration profile in the depth direction was obtained for the measuring surfaces at three points which were separated from each other by 1 mm or more in the direction of the wire axis.

[0098] -Thickness of coating layer and total number of measurement points in coating layer-

In the obtained concentration profile in the depth direction, the concentration profile was confirmed from the wire surface toward the center of the wire to obtain a distance from a depth position Z1 where the total of the Pd concentration C_{Pd} (atomic%) and the Ni concentration C_{Ni} (atomic%) reached 90 atomic% for the first time to a depth position Z2 where the total of C_{Pd} and C_{Ni} decreased below 90 atomic% for the first time ($Z2 > Z1$) as a measured thickness of the coating layer. Further, the total number of measurement points from the depth position Z1 to the depth position Z2 was obtained as the total number of measurement points in the coating layer. The arithmetic average value of numerical values obtained for the measuring surfaces at three points was employed as the thickness of the coating layer. It was confirmed that the total number of measurement points in the coating layer was 50 to 100 for the wires of the Examples.

Note that the depth measured by the AES analysis is obtained as the product of the sputtering rate and time. Since the sputtering rate is generally measured using a reference sample SiO_2 , the depth analyzed using AES is represented by an SiO_2 equivalent value. Thus, the unit for the thickness of the coating layer was in terms of SiO_2 .

[0099] -Average value X and total number of measurement points whose absolute deviation from average value X falls within predetermined range-

In the obtained concentration profile in the depth direction, the ratio of the Pd concentration C_{Pd} (atomic%) to the Ni concentration C_{Ni} (atomic%), $C_{\text{Pd}}/C_{\text{Ni}}$, for all measurement points in the coating layer was arithmetically averaged to obtain the average value X . Then, the absolute deviation from the average value X was calculated in the ratio $C_{\text{Pd}}/C_{\text{Ni}}$ for all measurement points in the coating layer, and the total number of measurement points whose absolute deviation from the average value X is $0.3X$ or less and the total number of measurement points whose absolute deviation from the average value X is $0.2X$ or less were obtained. The arithmetic average value of numerical values obtained for the measuring surfaces at three points was employed as the average value X .

[0100] -Slope of approximate straight line of C_{Pd} or C_{Ni} (difference between maximum value and minimum value in depth range of coating layer)-

C_{Pd} (atomic%) or C_{Ni} (atomic%) was linearly approximated by the method of least squares for all measurement points in the coating layer to obtain a difference (atomic%) between the maximum value and minimum value of the obtained approximate straight line in the depth range of the coating layer. Herein, if the average

value X was less than 1, C_{Ni} (atomic%) was linearly approximated by the method of least squares for all measurement points in the coating layer, and if the average value X was 1 or more, C_{Pd} (atomic%) was linearly approximated by the method of least squares for all measurement points in the coating layer. As the difference (atomic%) between the maximum value and the minimum value of the obtained approximate straight line in the depth range of the coating layer, the arithmetic average value of numerical values obtained for the measuring surfaces at three points was employed.

[0101] [Measurement of element content]

The contents of In, Ag, the first additive element, the second additive element, and the third additive element in the wire were detected as the concentration of elements contained in the entire wire by analyzing a liquid in which the bonding wire was dissolved with a strong acid using an ICP emission spectrometer or an ICP mass spectrometer. As an analysis device, ICP-OES ("PS3520UVDDII" manufactured by Hitachi High-Tech Corporation) or ICP-MS ("Agilent 7700x ICP-MS" manufactured by Agilent Technologies, Inc.) was used.

[0102] [FAB shape]

The evaluation of the FAB shape was performed by forming an FAB on a lead frame using a commercially available wire bonder and observing the FAB with a scanning electron microscope (SEM) (evaluation number N=100). The FAB was formed with a current value of 30 to 75 mA, an EFO gap of 762 μm , and a tail length of 254 μm while flowing an $\text{N}_2 + 5\% \text{H}_2$ gas at a flow rate of 0.4 to 0.6 L/min. The diameter of the FAB was in the range of 1.5 to 1.9 times the wire diameter. The FAB shape was determined to be favorable if it had a true spherical shape and determined

to be failure if it showed eccentricity, irregular shape, or poor melting. Evaluation was then performed in accordance with the following criteria.

[0103] Evaluation criteria:

- 5 ◎: 5 or less failures
- : 6 to 10 failures (no problem for practical use)
- ×: 11 or more failures

[0104] [Measurement of crystal orientation in cross-section of FAB]

- 10 The FAB was formed using the commercially available wire bonder under the conditions described in the section [FAB shape] noted above, and the crystal orientation was measured where the measuring surface was a cross-section of the FAB perpendicular to the compression-bonding direction.
- 15 In the present invention, the cross-section of the FAB perpendicular to the compression-bonding direction refers to a cross-section to be exposed by cutting the FAB along a dashed line A-A shown in FIG. 2, and the dashed line A-A serving as a reference was set at the position where the
- 20 diameter of the exposed cross-section became maximum. The EBSD method was used for the measurement, and the proportion of the crystal orientation <100> was calculated according to the above-mentioned procedure by using the analysis software included in the apparatus. The
- 25 proportion of the crystal orientation <100> in the cross-section of the FAB was determined by arithmetically averaging the values of the proportion obtained by measuring three FABs.

[0105] [Bond reliability of 2nd bonding part]

- 30 The bond reliability of the 2nd bonding part was evaluated by a High Temperature Storage Life Test (HTSL).

[0106] A sample was prepared by performing wedge bonding

onto leads of a lead frame using the commercially available wire bonder. The resultant sample was sealed by a commercially available thermosetting epoxy resin to manufacture a sample for testing the bond reliability of the 2nd bonding part. An Fe-42 atomic% Ni alloy lead frame plated with 1 to 3 μm Ni/Pd/Au was used for the lead frame. The manufactured sample for bond reliability evaluation was exposed to an environment with a temperature of 200°C using a high-temperature thermostatic device. The pull test on the wedge bonded part was performed every 500 hours, and a time until a value of pull force became half of the initial pull force was determined to be the bonding life of the 2nd bonding part. An arithmetic average value of measurement values of 50 wedge bonded parts randomly selected was used for the value of the pull force. The pull test after the High Temperature Storage Life Test was performed after removing the resin by acid treatment, and exposing the wedge bonded part. Evaluation was then performed in accordance with the following criteria.

[0107] Evaluation criteria:

◎◎: Bonding life of 2500 hours or more

◎: Bonding life of 2000 hours or more and less than 2500 hours

○: Bonding life of 1000 hours or more and less than 2000 hours

×: Bonding life of less than 1000 hours

[0108] [Bondability of 2nd bonding part]

The bondability of the 2nd bonding part was evaluated by a 2nd bonding window test. 2nd bonding window test is a test for determining the number of conditions with which the bonding was made possible among a total of 25 conditions for 2nd bonding. Specifically, the test is

conducted under a total of 25 conditions that indicates 5 stages of ultrasonic current at the time of 2nd bonding from 140 mA to 180 mA in 10 mA increments in the horizontal axis, and 5 stages of load at the time of 2nd bonding from 80 gf to 120 gf in 10 gf increments in the vertical axis.

[0109] [Table 1]

(Table 1)

		Ultrasonic current (mA)				
		140	150	160	170	180
Load (gf)	80					
	90					
	100					
	110					
	120					

[0110] This test was performed on each wire of Examples and Comparative Examples. Specifically, by using a commercially available wire bonder, 200 wires were bonded to leads of a lead frame for each condition. An Ag-plated lead frame was used as the lead frame, and bonding was performed at a stage temperature of 200°C under a flow of an N₂-5% H₂ gas at a flow rate of 0.5 L/min. The number of conditions with which continuous bonding was able to be performed without causing problems such as non-bonding or stop of the bonder was determined, and evaluated in accordance with the following criteria.

[0111] Evaluation criteria:

- ◎: 24 conditions or more
- : 22 or 23 conditions
- ×: 21 conditions or less

[0112] [Bond reliability of 1st bonding part]

The bond reliability of the 1st bonding part was evaluated by both of the High Temperature Storage Life Test (HTSL) and the Highly Accelerated Temperature and Humidity Stress Test (HAST).

[0113] -HTSL-

A sample was prepared by performing ball bonding on an electrode that was disposed by depositing an Al-1.0 mass% Si-0.5 mass% Cu alloy having a thickness of 2.0 μm on a silicon substrate on a general metal frame. The resultant sample was sealed by a commercially available thermosetting epoxy resin to manufacture a sample for testing the bond reliability of the 1st bonding part. The ball was formed under the conditions described in the section [FAB shape] noted above. The manufactured sample for bond reliability evaluation was exposed to an environment with a temperature of 200°C using a high-temperature thermostatic device. The shear test on the ball bonded part was performed every 500 hours, and a time until a value of shear force became half of the initial shear force was determined to be the bonding life of the 1st bonding part. An arithmetic average value of measurement values of 50 ball bonded parts randomly selected was used for the value of the shear force. The shear test after the High Temperature Storage Life Test was performed after removing the resin by acid treatment, and exposing the ball bonded part. Evaluation was then performed in accordance with the following criteria.

[0114] Evaluation criteria:

- ◎: Bonding life of 2000 hours or more
- : Bonding life of 1000 hours or more and less than 2000 hours
- ×: Bonding life of less than 1000 hours

[0115] -HAST-

The sample for testing the bond reliability of the 1st bonding part manufactured by the same procedure as that described above was exposed to a high-temperature and high-humidity environment with a temperature of 130°C and a relative humidity of 85% using an unsaturated type pressure

cooker tester and was biased with 7 V. The shear test on the ball bonded part was performed every 48 hours, and a time until a value of shear force became half of the initial shear force was determined to be the bonding life of the 1st bonding part. An arithmetic average value of measurement values of 50 ball bonded parts randomly selected was used for the value of the shear force. The shear test was performed after removing the resin by acid treatment, and exposing the ball bonded part. Evaluation was then performed in accordance with the following criteria.

[0116] Evaluation criteria:

◎: Bonding life of 384 hours or more

○: Bonding life of 240 hours or more and less than 384 hours

×: Bonding life of less than 240 hours

[0117] [Compression-bonding shape]

The evaluation of the compression-bonding shape of the 1st bonding part (the crushed shape of ball) was carried out by forming a ball using a commercially available wire bonder under the conditions described in the section [FAB shape] noted above, compression-bonding the ball onto an electrode that had been formed by depositing an Al-1.0 mass% Si-0.5 mass% Cu alloy film having a thickness of 2.0 μm on a Si substrate, and observing the bonded part from directly above by an optical microscope (the number of evaluations $N = 100$). In the evaluation of the crushed shape of ball, a case in which a crushed shape was close to true circle was determined to be favorable, and a case in which a crushed shape was an oval shape or a petal shape was determined to be failure. Evaluation was then performed in accordance with the following criteria.

[0118] Evaluation criteria:

◎: 0 failure

○: 1 to 3 failures

△: 4 or 5 failures

×: 6 or more failures

5 [0119] [Chip damage]

The evaluation of the chip damage was carried out by forming a ball using a commercially available wire bonder under the conditions described in the section [FAB shape] noted above, compression-bonding the ball onto an electrode that had been formed by depositing an Al-1.0 mass% Si-0.5 mass% Cu alloy film having a thickness of 2.0 μm on a Si substrate, dissolving the wire and the electrode with a chemical solution to expose the Si substrate, and observing the Si substrate directly below the bonded part by an optical microscope (the number of evaluations $N = 50$). Evaluation was then performed in accordance with the following criteria.

[0120] Evaluation criteria:

○: no crack or bonding traces

20 △: no crack, but there are sites where bonding traces were confirmed (3 sites or less)

×: other

[0121] The evaluation results of Examples and Comparative Examples are shown in Tables 2 to 4.

[0122]

[Table 2]

No.	Diameter um	Thickness of coating layer nm	Average value X ^{*1}	Measurement points with absolute deviation of 0.3X or less ^{*2} %	In concentr ation in wire ppm by mass	Ag concentr ation in wire ppm by mass	Measurement points with absolute deviation of 0.2X or less ^{*3} %	Difference between maximum value and minimum value of approximate straight line of C _{Pd} or C _{Ni} at%	Surface concentr ation of Au at%	First additive element (B, P, Mg) ppm by mass	Second additive element (Se, Te, As, Sb) ppm by mass	Third additive element (Ga, Ge) mass%	FAB shape	Bond reliability of 2nd bonding part	Initial bondability of 2nd bonding part	Bond reliability of 1st bonding part		Crushed shape	Chip damage
																HAST	HTSL		
Example	1	50	21	0.2	100	24	99	3					◎	◎	○	○	○	○	○
	2	50	130	0.5	50	8	50	15					◎	◎	○	○	○	○	○
	3	50	50	3.0	57	48	47	13					◎	◎	○	○	○	○	○
	4	50	110	6.1	68	46	64	13					◎	◎	○	○	○	○	○
	5	50	70	34.7	88	68	84	19					◎	◎	○	○	○	○	○
	6	50	15	9.0	82	73	69	11					◎	◎	○	○	○	○	○
	7	50	45	1.5	61	100	55	10					○	◎	○	○	○	○	○
	8	50	64	0.4	51	77	31	7					○	◎	○	○	○	○	○
	9	50	35	0.8	80	15	53	13					◎	◎	○	○	○	○	○
	10	50	10	1.0	80	64	61	19					◎	◎	○	○	○	○	○
	11	50	16	3.8	79	1	59	16					○	◎	○	○	○	○	○
	12	50	68	22.8	77	92	74	2					◎	◎	○	○	○	○	○
	13	50	62	1.3	51	85	51	18					◎	◎	○	○	○	○	○
	14	50	21	0.8	70	20	58	18					◎	◎	○	○	○	○	○
	15	50	42	2.0	79	69	66	4					◎	◎	○	○	○	○	○
	16	50	32	4.0	97	71	58	16	10				◎	◎	◎	○	○	○	○
	17	50	71	0.6	74	76	60	8	38				◎	◎	◎	○	○	○	○
	18	50	22	1.4	64	61	52	11	45				○	◎	◎	○	○	○	○
	19	50	19	0.8	85	54	78	8	90				◎	◎	◎	○	○	○	○
	20	50	118	3.3	73	40	42	8		B:1			○	◎	◎	○	◎	○	○
	21	50	53	2.1	70	89	43	5		P:55			◎	◎	○	○	○	○	○
	22	50	102	1.5	71	10	63	13		Mg:100			◎	◎	○	○	○	◎	○
	23	50	89	0.8	65	76	60	6		B:25, P:45			◎	◎	○	○	◎	◎	○

*1 Average value X of ratio of Pd concentration C_{Pd} (atomic%) to Ni concentration C_{Ni} (atomic%) for all measurement points in coating layer

*2 Proportion (%) of total number of measurement points in coating layer whose absolute deviation from average value X is 0.3X or less relative to total number of measurement points in coating layer

*3 Proportion (%) of total number of measurement points in coating layer whose absolute deviation from average value X is 0.2X or less relative to total number of measurement points in coating layer

[0123]

[Table 3]

No.	Diameter	Thickness of coating layer	Average value X^{*1}	Measurement points with absolute deviation of 0.3X or less ^{*2}	In concentration in wire	Ag concentration in wire	Measurement points with absolute deviation of 0.2X or less ^{*3}	Difference between maximum value and minimum value of approximate straight line of C_{Pd} or C_{Ni}	Surface concentration of Au	First additive element (B, P, Mg)	Second additive element (Se, Te, As, Sb)	Third additive element (Ga, Ge)	FAB shape	Bond reliability of 2nd bonding part	Initial bondability of 2nd bonding part	Bond reliability of 1st bonding part		Crushed shape	Chip damage
					ppm by mass	ppm by mass	%	at%	at%	ppm by mass	ppm by mass	mass%				HAST	HTSL		
Example	24	50	13	0.7	100	49	44	5			Se:21		◎	◎	◎	◎	◎	◎	◎
	25	50	26	6.5	97	87	74	8			Te:8		◎	◎	◎	◎	◎	◎	◎
	26	50	87	3.7	84	34	72	14			As:1		◎	◎	◎	◎	◎	◎	◎
	27	50	51	21.5	88	58	50	3			Sb:100		◎	◎	◎	◎	◎	◎	◎
	28	50	53	0.3	63	42	50	8			Se:5Te:8		◎	◎	◎	◎	◎	◎	◎
	29	50	25	0.8	75	35	73	11				Ga:0.11	◎	◎	◎	◎	◎	◎	◎
	30	50	57	0.3	72	36	57	9				Ga:0.4	◎	◎	◎	◎	◎	◎	◎
	31	50	108	0.5	58	17	44	6				Ge:1.5	◎	◎	◎	◎	◎	◎	◎
	32	50	120	1.1	90	82	67	7			Ga:0.15Ge:0.15		◎	◎	◎	◎	◎	◎	◎
	33	50	61	0.7	74	16	56	9		P:65			◎	◎	◎	◎	◎	◎	◎
	34	50	91	7.3	95	59	68	11			Se:80		◎	◎	◎	◎	◎	◎	◎
	35	50	59	0.4	88	57	82	7				Ge: 0.2	◎	◎	◎	◎	◎	◎	◎
	36	50	32	0.5	58	50	44	16		P:70	Te:6	Ga:0.4	◎	◎	◎	◎	◎	◎	◎
	37	50	20	9.0	52	50	36	13					◎	◎	◎	◎	◎	◎	◎
	38	50	55	3.0	89		64	2					◎	◎	◎	◎	◎	◎	◎
	39	50	84	4.0	88		95	10					◎	◎	◎	◎	◎	◎	◎
	40	50	60	1.9	57		32	20					◎	◎	◎	◎	◎	◎	◎
	41	50	120	2.6	82		500	3					◎	◎	◎	◎	◎	◎	◎
	42	50	45	1.6	80	50	65	5					◎	◎	◎	◎	◎	◎	◎
	43	50	75	0.8	95		64	11					◎	◎	◎	◎	◎	◎	◎
	44	50	65	1.2	79	25	68	8		Mg:50			◎	◎	◎	◎	◎	◎	◎
	45	50	80	11.5	95		113	9					◎	◎	◎	◎	◎	◎	◎
	46	50	32	0.8	64		25	17		P:50	Te:9	Ga:0.8	◎	◎	◎	◎	◎	◎	◎
	47	50	85	1.2	81		56	6		P: 85	Se:18	Ge: 0.3	◎	◎	◎	◎	◎	◎	◎
	48	50	72	3.0	71		416	8		B: 18		Ge: 0.9	◎	◎	◎	◎	◎	◎	◎
	49	50	65	0.5	77	83	150	7			As: 52	Ga: 0.2	◎	◎	◎	◎	◎	◎	◎
	50	50	60	0.4	52	9	20	18			Te: 21	Ge: 1.3	◎	◎	◎	◎	◎	◎	◎
Comparative Example	1	50	9	3.0	82	25	57	15					x	x	◎	◎	x	x	◎
	2	50	131	0.5	68	50	57	10					x	x	◎	◎	x	x	◎
	3	50	85	0.1	66		50	21					x	◎	x	◎	x	x	◎
	4	50	65	40.0	91	63	82	5					x	x	◎	◎	x	x	◎
	5	50	80	1.9	49	5	7	8					x	x	◎	◎	x	x	◎
	6	50	46	1.3	65		51	18					◎	x	◎	◎	◎	◎	◎

*1 Average value X of ratio of Pd concentration C_{Pd} (atomic%) to Ni concentration C_{Ni} (atomic%) for all measurement points in coating layer

*2 Proportion (%) of total number of measurement points in coating layer whose absolute deviation from average value X is 0.3X or less relative to total number of measurement points in coating layer

*3 Proportion (%) of total number of measurement points in coating layer whose absolute deviation from average value X is 0.2X or less relative to total number of measurement points in coating layer

[0124] [Table 4]

No.	Diameter um	Thickness of coating layer nm	Average value X^{*1}	Measurement points with absolute deviation of 0.3X or less ^{*2}	In concentr ation in wire ppm by mass.	Ag concentr ation in wire ppm by mass	Measurement points with absolute deviation of 0.2X or less ^{*3}	Difference between maximum value and minimum value of approximate straight line of C_{Pd} or C_{Ni} at%	Surface concentr ation of Au at%	First additive element (B, P, Mg) ppm by mass	Second additive element (Se, Te, As, Sb) ppm by mass	Third additive element (Ga, Ge) mass%	Crystal orientation <100> in cross- section of FAB %	Refining heat treatment temperature °C	FAB shape	Crushed shape
Example	51	50	15	0.6	62	50	60	10					70	410	○	◎
	52	50	55	2.0	70	100	65	12					42	480	◎	○
	53	50	18	0.4	55	1	52	8					58	440	○	◎
	54	50	45	2.5	80	2	78	13	35				55	410	◎	◎
	55	50	40	1.0	85	55	82	6	40				32	510	◎	○
	56	50	80	3.0	88	64	85	6					82	460	◎	◎
	57	50	22	0.8	56	72	51	22					27	530	○	△
	58	50	85	1.2	31		73	6					63	450	◎	◎
	59	50	72	3.0	28		67	8					75	490	○	◎
	60	50	65	0.5	33	83	74	7					26	450	◎	△
	61	50	60	0.4	31	91	48	18					35	460	◎	○

^{*1} Average value X of ratio of Pd concentration C_{Pd} (atomic%) to Ni concentration C_{Ni} (atomic%), C_{Pd}/C_{Ni} for all measurement points in coating layer
^{*2} Proportion (%) of total number of measurement points in coating layer whose absolute deviation from average value X is 0.3X or less relative to total number of measurement points in coating layer
^{*3} Proportion (%) of total number of measurement points in coating layer whose absolute deviation from average value X is 0.2X or less relative to total number of measurement points in coating layer

[0125] All of the wires of Example Nos. 1 to 50 included the coating layer that satisfied all of the conditions (1)

to (3) specified in this specification and contained at least one of In and Ag in an amount of 1 ppm by mass or more relative to the entire wire, and it was confirmed that they achieved a favorable FAB shape and a favorable bond reliability of the 2nd bonding part. In particular, it was confirmed that the wires satisfying more preferable range for one or more of the conditions (1) to (3) and the conditions (i) and (ii) described above tended to achieve a particularly favorable bond reliability of the 2nd bonding parts. The wires of Example Nos. 5, 12, 15, 17, 19, 23 27, 34, 35, 41, 42, 44, 48 and 49 achieved an especially excellent bond reliability of the 2nd bonding parts. It was confirmed that, at least for the wires in these Examples, when defining the average value of C_{Pd} (atomic%) for all measurement points in the coating layer as X_{Pd} , the total number of measurement points in the coating layer whose absolute deviation from the average value X_{Pd} was $0.1X_{Pd}$ or less was 50% or more relative to the total number of measurement points in the coating layer, and when defining the average value of C_{Ni} (atomic%) for all measurement points in the coating layer as X_{Ni} , the total number of measurement points in the coating layer whose absolute deviation from the average value X_{Ni} was $0.1X_{Ni}$ or less was 50% or more relative to the total number of measurement points in the coating layer.

Further, it was confirmed that the wires of Example Nos. 16 to 19, 33 to 36, 43 to 46, and 50 containing Au at the surface thereof exhibited a particularly excellent initial bondability of the 2nd bonding part.

Furthermore, it was confirmed that the wires of Example Nos. 20 to 23, 33, 36, 44 to 48 containing the first additive element of 1 ppm by mass or more in total achieved an especially excellent compression-bonding shape

of the 1st bonding part. It was confirmed that the wires of Example Nos. 24 to 28, 34, 36, 45, 46, 49, and 50 containing the second additive element of 1 ppm by mass or more in total achieved an especially excellent bond reliability of the 1st bonding part in a high-temperature and high-humidity environment. It was confirmed that the wires of Example Nos. 29 to 32, 35, 36, 46 to 50 containing the third additive element of 0.011% by weight or more in total achieved an especially excellent bond reliability of the 1st bonding part in a high-temperature environment.

On the other hand, the wires of Comparative Example Nos. 1 to 6 included the coating layer that did not satisfy at least one of the conditions (1) to (3) specified in this specification or had the contents of In and Ag of less than 1 ppm by mass relative to the entire wire, and it was confirmed that they were poor in any one of the FAB shape and the bond reliability of the 2nd bonding parts.

[0126] It was confirmed that a favorable compression-bonding shape of the 1st bonding part was achieved by a wire ensuring that, when forming an FAB by using the wire and then measuring crystal orientations in a cross-section of the FAB perpendicular to a compression-bonding direction, a proportion of a crystal orientation <100> angled at 15° or less to the compression-bonding direction was 30% or more (Example Nos. 51 to 61). In particular, it was confirmed that the wire ensuring the proportion of the crystal orientation <100> of 50% or more was capable of achieving an especially excellent compression-bonding shape of the 1st bonding part (Example Nos. 51, 53, 54, 56, 58, and 59).

[0127] [Description of reference signs]

- 1 bonding wire (wire)
- 2 measuring surface

	X	center of width of wire
	W	width of wire (wire diameter)
	w_a	width of measuring surface
	l_a	length of measuring surface
5	10	FAB
	Z	compression-bonding direction of FAB

CLAIMS

1. A bonding wire for semiconductor devices, the bonding wire comprising:

5 a core material of Cu or Cu alloy; and

a coating layer having a total concentration of Pd and Ni of 90 atomic% or more formed on a surface of the core material, wherein

10 in a concentration profile in a depth direction of the wire obtained by performing measurement using Auger electron spectroscopy (AES) so that the number of measurement points in the depth direction is 50 or more for the coating layer,

15 a thickness of the coating layer is 10 nm or more and 130 nm or less,

an average value X is 0.2 or more and 35.0 or less where X is defined as an average value of a ratio of a Pd concentration C_{Pd} (atomic%) to an Ni concentration C_{Ni} (atomic%), C_{Pd}/C_{Ni} , for all measurement points in the coating layer,

20 a total number of measurement points in the coating layer whose absolute deviation from the average value X is $0.3X$ or less is 50% or more relative to a total number of measurement points in the coating layer, and

25 the bonding wire satisfies at least one of the following conditions (i) and (ii):

(i) a concentration of In relative to the entire wire is 1 ppm by mass or more and 100 ppm by mass or less; and

30 (ii) a concentration of Ag relative to the entire wire is 1 ppm by mass or more and 500 ppm by mass or less.

2. The bonding wire according to claim 1, wherein the total number of measurement points in the coating layer

whose absolute deviation from the average value X is $0.2X$ or less is 50% or more relative to the total number of measurement points in the coating layer.

5 3. The bonding wire according to claim 1 or 2, wherein
when linearly approximating C_{Pd} or C_{Ni} by the method of
least squares for all measurement points in the coating
layer, a difference between a maximum value and a minimum
value of the obtained approximate straight line in a depth
10 range of the coating layer is 20 atomic% or less.

4. The bonding wire according to any one of claims 1 to
3, wherein the concentration profile in the depth direction
of the wire is obtained by performing the measurement using
15 AES under the following <Condition> while digging down the
wire from its surface in the depth direction by Ar
sputtering:

 <Condition> a center of width of a measuring surface
is aligned with a center of width of the wire, the width of
20 the measuring surface is 5% or more and 15% or less of a
diameter of the wire, and a length of the measuring surface
is five times the width of the measuring surface.

5. The bonding wire according to any one of claims 1 to
25 4, wherein the bonding wire contains Au at a surface
thereof.

6. The bonding wire according to claim 5, wherein a
concentration of Au at the surface of the wire is 10
30 atomic% or more and 90 atomic% or less.

7. The bonding wire according to claim 6, wherein the
concentration of Au at the surface of the wire is measured

using AES under the following <Condition>:

<Condition> a center of width of a measuring surface is aligned with a center of width of the wire, the width of the measuring surface is 5% or more and 15% or less of a diameter of the wire, and a length of the measuring surface is five times the width of the measuring surface.

8. The bonding wire according to any one of claims 1 to 7, wherein when forming a free air ball (FAB: Free Air Ball) by using the wire and then measuring crystal orientations in a cross-section of the FAB perpendicular to a compression-bonding direction, a proportion of a crystal orientation <100> angled at 15° or less to the compression-bonding direction is 30% or more.

9. The bonding wire according to claim 8, wherein the proportion of the crystal orientation <100> angled at 15° or less to the compression-bonding direction is 50% or more.

10. The bonding wire according to any one of claims 1 to 9, wherein

the bonding wire contains one or more elements selected from the group consisting of B, P and Mg (hereinafter referred to as a "first additive element"), and

a total concentration of the first additive element is 1 ppm by mass or more and 100 ppm by mass or less relative to the entire wire.

11. The bonding wire according to any one of claims 1 to 10, wherein

the bonding wire contains one or more elements selected from the group consisting of Se, Te, As and Sb (hereinafter referred to as a "second additive element"), and

5 a total concentration of the second additive element is 1 ppm by mass or more and 100 ppm by mass or less relative to the entire wire.

12. The bonding wire according to any one of claims 1 to
10 11, wherein

the bonding wire contains one or more elements selected from the group consisting of Ga and Ge (hereinafter referred to as a "third additive element"), and

15 a total concentration of the third additive element is 0.011% by mass or more and 1.5% by mass or less relative to the entire wire.

13. A semiconductor device comprising the bonding wire
20 according to any one of claims 1 to 12.